

Reconfigurable Three-Mode Converter for Flexible Mode Division Multiplexing Optical Networks

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Abstract—Mode converters with reconfigurable functionality are essential for enabling flexible operation in modern mode division multiplexing (MDM) technology-based optical networks. In this paper, we propose a novel reconfigurable three-mode converter capable of converting the TE_0 , TE_1 , and TE_2 modes to any desired output mode, such as TE_0 , TE_1 , or TE_2 , for use in MDM optical communication system. Our device utilizes thermo-optic (TO) effects and consists of cascaded Y-junctions and Mach-Zehnder interferometers (MZIs), comprising two three-arm mode converters and one two-arm mode converter. The analytical and numerical verification of our device demonstrates its efficient operation, and the measurement results align favorably with the simulated performance. Our photonic integrated circuit (PIC) compatible fabricated device exhibits the mode conversion efficiency (MCE) of higher than 92.5% with maximum insertion loss (IL) of 8.3 dB and crosstalks (XTs) lower than -18.9 dB in the entire C band (1.530–1.565 μm). Our three-mode energy efficient and polarization-insensitive converter offers promising potential in enhancing the flexibility of MDM optical networks, making it a viable candidate for future development and deployment.

Index Terms—Mode division multiplexing (MDM), flexible optical networks, capacity issue, transfer matrices, bidirectional.

I. INTRODUCTION

IN ORDER to accommodate mobile broadband networks, Big Data, Internet of Things (IoT), massive cloud computing, automated vehicles, and other broadband applications, there is a tremendous need to expand the data capacity of traditional optical networks [1], [2], [3]. MDM is regarded as the emerging and the most effective solution to address this capacity issue, along with wave length division multiplexing (WDM) [4], [5]. MDM system utilizes few-mode fiber (FMF) to carry various optical modes or mode groups where each mode is considered as an independent WDM data channel and the increased number of modes indicate increasing data capacity [6], [7], [8]. To deal with

distinct modes, MDM system requires different optical devices, e.g., mode converters [9], [10], [11], mode mux-demux [12], [13], [14], mode filters [15], [16], [17], mode switches [18], [19], [20], etc., capable of handling several modes [21], [22]. Mode converter is a basic building component for MDM system [23] and improves the efficiency of optical networks and utilization of resources [9], [24]. But mode converters capable of dynamically converting a mode order to any desired order will be required for the fully flexible MDM networks [25], [26]. Moreover, optical waveguide-based photonic integrated circuit (PIC), also known as planar lightwave circuit (PLC), technology is preferable compared to bulk and fiber optics. Their popularity emerged due to their compactness, compatibility with fiber-based devices, and the ability to integrate optical (and electronic) components on a single chip [27], [28]. Over the years various PIC mode converters have been developed where the most of them are passive [29], [30], [31], [32], [33], [34], [35], [36], [37], [38], [39], [40], [41], [42], [43], [44], [45] and some have switchable operation [46], [47], [48], [49], [50], [51], [52], [53], [54]. The mode switch and converter reported in [46] and [47] support only transverse magnetic (TM) modes. The electro-optic device introduced in [48] switches between two transverse electric (TE) modes (TE_{11} and TE_{21}). The TE_0 and TE_2 modes can be converted to one another by the multi-function device stated by Kazi [49] while it is not able to handle TE_1 mode. A silicon-Sb₂S₃ hybrid materials based tunable mode converter is theoretically studied in [50]. The three-mode and four-mode converters reported in [51] and [52] are based on cascaded MMIs-MZIs and cross-connected Y-junctions, respectively. A reconfigurable mode converter using cascaded waveguide switches is demonstrated in [53]. The four-mode converter, suggested in [54], is implemented using MZI with vertically-separated arms. However, the most of the above-mentioned switchable mode converters consume relatively large power to activate the heater electrodes and are polarization-dependent. For large scale integration, also for cost effectiveness, low power optical devices are required [55]. On the other hand, polarization-independent devices are able to handle the uncertain polarization of fiber networks, eliminate the use of polarization splitter and/or polarization combiner and leverage the polarization division multiplexing (PDM) degree of freedom [56], [57], [58]. Furthermore, some of the devices possess complex structure, e.g., multilayer waveguide, inverse design, 3D composite waveguide, etc., which makes them complicated to fabricate (require multi-step lithography and/or expensive electron beam

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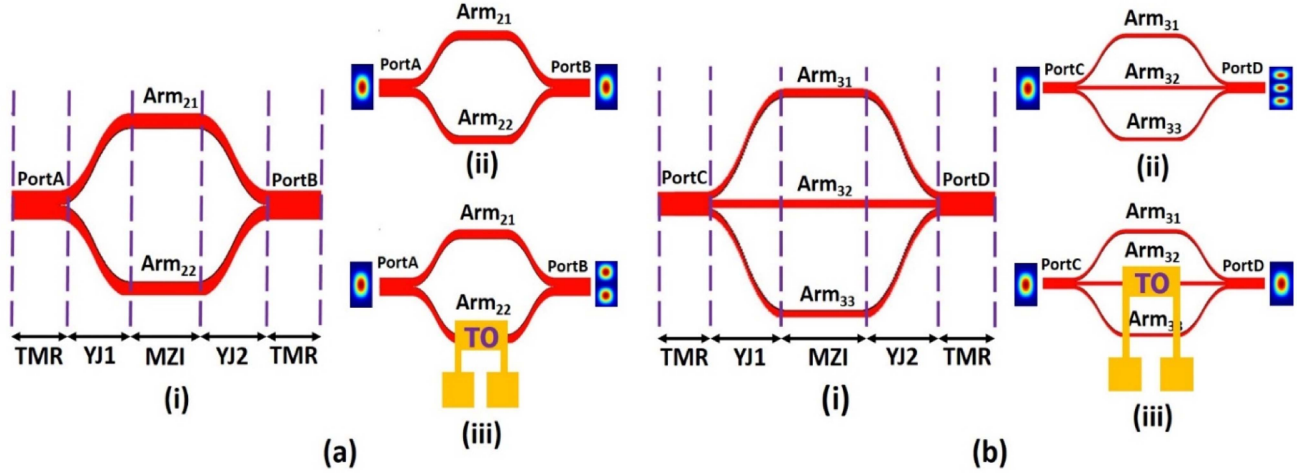


Fig. 1. (a) Operation of TWMC (i) structure of TWMC (ii) normal operation (iii) operation with TO active and (b) operation of THMC (i) structure of THMC (ii) normal operation (iii) operation with TO active.

lithography (EBL)/laser writing technique) or performing worse [58], [59].

In this article, we proposed and demonstrated a unique three-mode converter structure consisting of cascaded Y-junctions and MZIs based mode converters. The device is fabricated using traditional low-cost ultraviolet lithography (UVL) process [58]. Micro-heater electrodes are employed for controlling the phase difference of the mode array propagating along the MZI arms. MZI based Multiplexer/demultiplexer (Mux/Demux) are utilized, as in [12], for launching the single-mode inputs and getting the outputs. With such a configuration, the device can convert the three TE modes, such as fundamental mode (TE_0), first-order mode (TE_1) and second-order mode (TE_2), launched at the input port to any of the TE_0 , TE_1 and TE_2 modes at the output port by tuning the ON/OFF state of the heater electrodes. Analytical validation is employed to evaluate the device operation and the simulated and experimental results support the device's performance. The measured ILs, for all various conversions of the device, are below 8.3 dB and XTs are lower than -18.9 dB with MCE more than 92.5% over the entire C band. Furthermore, the device is almost polarization-insensitive and consume relatively low power (Maximum 8.4 mW) to turn on the electrodes. Our proposed mode converter has a great opportunity to be used in fully flexible MDM optical networks.

II. PRINCIPLE OF OPERATION

The device is constructed by the integration of two-arm and three-arm mode converters (TWMC and THMC). The TWMC, (Fig. 1(a)), possesses three-mode region (TMR), two Y-junctions (YJs) and a balanced two-arm MZI where THMC, (Fig. 1(b)), composed of TMR, two YJs and an unbalanced three-arm MZI. In TWMC, the MZI possesses same path length for Arm_{21} and Arm_{22} . The MZI has equal path length for Arm_{31} and Arm_{33} , in THMC, and holds a path difference of ΔL with compare to Arm_{32} that initiates a phase difference of π [49].

For both mode converters, YJ1, MZI and YJ2 act as the power splitter, phase shifter and power combiner, respectively. TO effect is used to Arm_{22} of TWMC and Arm_{32} of THMC to originate the additional phase change required.

The operation of TWMC and THMC can be easily understood from the overall transfer matrices which are obtained from the multiplication of the transfer matrices of different parts of the converters [60], [61]. In TWMC, YJ1 is the first part and divides the launched light (fundamental or first-order mode) into two portions [62]. The output fields of the two arms are in phase and have equal magnitude for fundamental mode and holds a phase difference of 180° for first-order mode. Hence, the transfer matrices of the YJ1 of TWMC for the fundamental and first-order modes are as follows [62]:

$$\begin{bmatrix} \sqrt{1/2} \\ \sqrt{1/2} \end{bmatrix}$$

and

$$\begin{bmatrix} \sqrt{1/2} \\ -\sqrt{1/2} \end{bmatrix}$$

The second part of TWMC is the phase shifter (MZI). The transfer matrix of the two arm MZI is [60], [61]

$$\begin{bmatrix} \exp(-i\beta\Delta L) & 0 \\ 0 & \exp(-i\beta\Delta L) \end{bmatrix}$$

where β is the propagation constant and ΔL is the path difference between the arms. From multiplication of the transfer matrices, the overall transfer matrix of the TWMC is

$$P_B = \begin{bmatrix} P_{21} \\ P_{22} \end{bmatrix} = \begin{bmatrix} \exp(-i\beta\Delta L) & 0 \\ 0 & \exp(-i\beta\Delta L) \end{bmatrix} \cdot \begin{bmatrix} \sqrt{1/2} \\ \pm\sqrt{1/2} \end{bmatrix} P_A \quad (1)$$

where P_{21} and P_{22} are the e-field magnitude at the output ends of two MZI arms, P_A is the e-field magnitude at PortA and P_B is the e-field magnitude at PortB.

Now if TE_0 mode is input with no TO, it is split into two portions into the symmetric arms, Arm₂₁ and Arm₂₂, with no phase change ($\beta \cdot \Delta L = 0$). Then the transfer matrix becomes,

$$P_{B0(off)} = \begin{bmatrix} P_{21} \\ P_{22} \end{bmatrix} = \begin{bmatrix} 1 & 0 \\ 0 & 1 \end{bmatrix} \cdot \begin{bmatrix} \sqrt{1/2} \\ \sqrt{1/2} \end{bmatrix} P_A \quad (2)$$

where $P_{B0(off)}$ is the e-field magnitude at PortB when fundamental mode is launched with no TO. Equation (2) indicates that there is no mode conversion for fundamental mode when TO remains inactive (Fig. 1(a)(ii)).

When TE_0 mode is input with TO on, a phase change of π ($\beta \cdot \Delta L = \pi$) is introduced to the Arm₂₂. Then the transfer matrix becomes

$$P_{B0(on)} = \begin{bmatrix} P_{21} \\ P_{22} \end{bmatrix} = \begin{bmatrix} 1 & 0 \\ 0 & -1 \end{bmatrix} \cdot \begin{bmatrix} \sqrt{1/2} \\ \sqrt{1/2} \end{bmatrix} P_A \quad (3)$$

where $P_{B0(on)}$ is the e-field magnitude at PortB when fundamental mode is launched with TO turned on. Equation (3) shows a TE_0 to TE_1 mode conversion for TO in activated state (Fig. 1(a)(iii)).

Similarly, for TE_1 mode with heater off and on, the transfer matrices are as follows:

$$P_{B1(off)} = \begin{bmatrix} P_{21} \\ P_{22} \end{bmatrix} = \begin{bmatrix} \sqrt{1/2} \\ -\sqrt{1/2} \end{bmatrix} P_A \quad (4)$$

and

$$P_{B1(on)} = \begin{bmatrix} P_{21} \\ P_{22} \end{bmatrix} = \begin{bmatrix} \sqrt{1/2} \\ \sqrt{1/2} \end{bmatrix} P_A \quad (5)$$

where $P_{B1(off)}$ and $P_{B1(on)}$ are the e-field magnitude at PortB when first-order mode is launched with TO turned off and on, respectively.

On the other hand, following the same procedure [62], the transfer matrices of the YJ1 of THMC for the fundamental and second-order modes are

$$\begin{bmatrix} \sqrt{1/3} \\ \sqrt{1/3} \\ \sqrt{1/3} \end{bmatrix}$$

and

$$\begin{bmatrix} -\sqrt{1/3} \\ \sqrt{1/3} \\ -\sqrt{1/3} \end{bmatrix}$$

The transfer matrix of the three-arm MZI is [60], [61]

$$\begin{bmatrix} \exp(-i\beta\Delta L) & 0 & 0 \\ 0 & \exp(-i\beta\Delta L) & 0 \\ 0 & 0 & \exp(-i\beta\Delta L) \end{bmatrix}$$

From the multiplication, the overall transfer matrix of THMC is as follows:

$$P_D = \begin{bmatrix} P_{31} \\ P_{32} \\ P_{33} \end{bmatrix} = \begin{bmatrix} \exp(-i\beta\Delta L) & 0 & 0 \\ 0 & \exp(-i\beta\Delta L) & 0 \\ 0 & 0 & \exp(-i\beta\Delta L) \end{bmatrix} \cdot \begin{bmatrix} \pm\sqrt{1/3} \\ \sqrt{1/3} \\ \pm\sqrt{1/3} \end{bmatrix} P_C \quad (6)$$

where P_{31} , P_{32} , and P_{33} are the e-field magnitude at the output end of three MZI arms, P_C is the e-field magnitude at PortC and P_D is the e-field magnitude at PortD.

Then for TE_0 mode with no TO, each of Arm₃₁ and Arm₃₃ has a phase difference of π ($\beta \cdot \Delta L = \pi$) with Arm₃₂ and the transfer matrix becomes

$$P_{D0(off)} = \begin{bmatrix} P_{31} \\ P_{32} \\ P_{33} \end{bmatrix} = \begin{bmatrix} -1 & 0 & 0 \\ 0 & 1 & 0 \\ 0 & 0 & -1 \end{bmatrix} \cdot \begin{bmatrix} \sqrt{1/3} \\ \sqrt{1/3} \\ \sqrt{1/3} \end{bmatrix} P_C = \begin{bmatrix} -\sqrt{1/3} \\ \sqrt{1/3} \\ -\sqrt{1/3} \end{bmatrix} P_C \quad (7)$$

where $P_{D0(off)}$ is the e-field magnitude at PortD when fundamental mode is launched with TO off. Equation (7) indicates that there occurs TE_0 to TE_2 mode conversion for fundamental mode when TO remains inactive (Fig. 1(b)(ii)).

When TO is on for TE_0 , an additional phase difference of π is originated into the Arm₃₂ and now there is no phase difference ($\beta \cdot \Delta L = 0$) among the arms. The transfer matrix becomes

$$P_{D0(on)} = \begin{bmatrix} P_{31} \\ P_{32} \\ P_{33} \end{bmatrix} = \begin{bmatrix} 1 & 0 & 0 \\ 0 & 1 & 0 \\ 0 & 0 & 1 \end{bmatrix} \cdot \begin{bmatrix} \sqrt{1/3} \\ \sqrt{1/3} \\ \sqrt{1/3} \end{bmatrix} P_C = \begin{bmatrix} \sqrt{1/3} \\ \sqrt{1/3} \\ \sqrt{1/3} \end{bmatrix} P_C \quad (8)$$

where $P_{D0(on)}$ is the e-field magnitude at PortD when fundamental mode is launched with TO active. Equation (8) indicates that there is no mode conversion for fundamental mode when TO is activated (Fig. 1(b)(iii)).

Similarly, for TE_2 mode with heater off and on, the transfer matrices are as follows:

$$P_{D2(off)} = \begin{bmatrix} P_{31} \\ P_{32} \\ P_{33} \end{bmatrix} = \begin{bmatrix} -1 & 0 & 0 \\ 0 & 1 & 0 \\ 0 & 0 & -1 \end{bmatrix} \cdot \begin{bmatrix} -\sqrt{1/3} \\ \sqrt{1/3} \\ -\sqrt{1/3} \end{bmatrix} P_C = \begin{bmatrix} \sqrt{1/3} \\ \sqrt{1/3} \\ \sqrt{1/3} \end{bmatrix} P_C \quad (9)$$

and

$$P_{D2(on)} = \begin{bmatrix} P_{31} \\ P_{32} \\ P_{33} \end{bmatrix} = \begin{bmatrix} 1 & 0 & 0 \\ 0 & 1 & 0 \\ 0 & 0 & 1 \end{bmatrix} \cdot \begin{bmatrix} -\sqrt{1/3} \\ \sqrt{1/3} \\ -\sqrt{1/3} \end{bmatrix} P_C$$

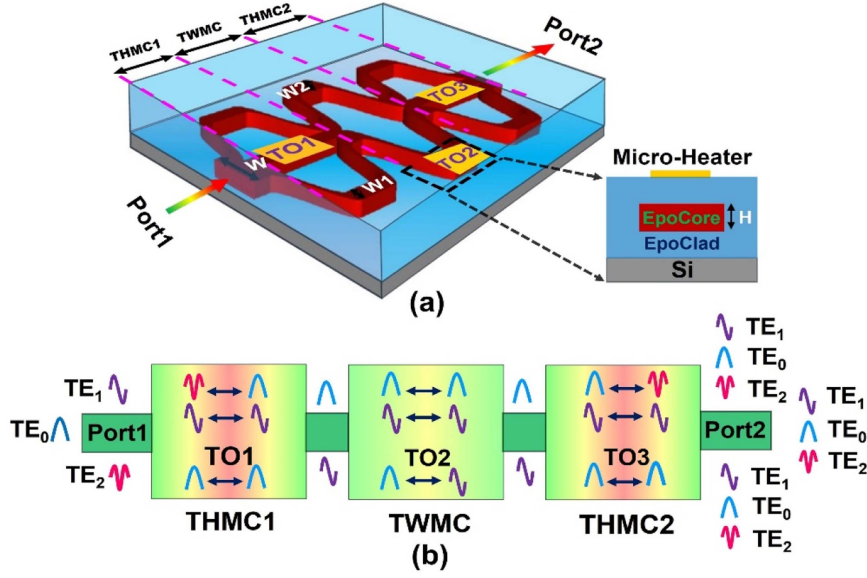


Fig. 2. Proposed reconfigurable mode converter. (a) Device structure and (b) schematic diagram.

$$= \begin{bmatrix} -\sqrt{1/3} \\ \sqrt{1/3} \\ -\sqrt{1/3} \end{bmatrix} P_C \quad (10)$$

where $P_{D2(off)}$ and $P_{D2(on)}$ are the e-field magnitude at PortD when second-order mode is launched with TO turned off and on, respectively.

III. DEVICE STRUCTURE AND FUNCTION

The structure and schematic diagram of the reconfigurable mode converter are illustrated in Fig. 2. The device consists of two bidirectional THMCs (THMC1 and THMC2) sandwiched by a TWMC. The middle arm of THMC1 and THMC2 is equipped with heater electrodes TO1 and TO3, respectively, while the bottom arm of TWMC has heater electrode TO2. THMCs convert the fundamental mode (TE_0) to the second-order mode (TE_2) and reciprocal, while the first-order mode (TE_1) remains unchanged. TWMC is also reciprocal and allows the TE_0 and TE_1 modes to pass through it directly when input at any of its ends. When TO1 and TO3 are activated, THMC1 and THMC2, respectively, allow the TE_0 and TE_2 modes to pass through them without any mode conversion. By turning ON TO2, TWMC converts TE_0 to TE_1 and vice versa. THMC1 is operated in such a way that no TE_2 mode is generated at its output port. With this configuration, the device can convert among TE_0 , TE_1 , and TE_2 modes.

For example, we consider TE_0 to TE_1 mode conversion. TE_0 mode is launched at the input Port1 and approaches to the input stem of THMC1. Then TO1 is turned ON and hence, there is no mode conversion by THMC1 and TE_0 comes out of it and reaches to the input stem of TWMC. Now, TO2 is activated and hence, a TE_0 to TE_1 mode conversion occurs by TWMC. TE_1 mode comes to the input stem of THMC2. In this stage, TO3 remains turned OFF and hence TE_1 mode passes

directly through THMC2 and finally arrives at the output Port2. Following this procedure, our device can arbitrarily convert any of TE_0 , TE_1 and TE_2 modes to any of TE_0 , TE_1 and TE_2 modes.

IV. DESIGN AND SIMULATION RESULTS

The proposed mode converter is designed with commercially available EpoCore and EpoClad polymer materials as the core and cladding, respectively. The height and width of the Y-junction stem are selected for supporting three modes such as TE_0 , TE_1 and TE_2 modes. The arm dimension of THMC1 and THMC2 support only TE_0 mode. The stem width and height of the device are $W = 14.25 \mu\text{m}$ and $H = 4.75 \mu\text{m}$ to support three modes (Fig. 2(a)). The arm width the of THMC1 and THMC2 is $W_1 = 4.75 \mu\text{m}$ and that of the TWMC is $W_2 = 7.125 \mu\text{m}$. The branch separation angles of the Y-junctions for the THMCs and TWMC are set to 0.8° and 0.88° , respectively, to minimize excess loss. S-bends are used to design the Y-junctions so that there is sufficient arms separation for fabrication tolerance. Each MZI arm of the THMCs has a length of $2000 \mu\text{m}$ and that for TWMCs is $1500 \mu\text{m}$ which is enough to introduce the heater electrodes. The device has a total length of 17.35 mm which could be reduced significantly using SOI (silicon-on-insulator) or LNOI (lithium niobate on insulator) based high-index-contrast materials [63].

The device operation can be easily understood by monitoring the mode positions along the propagation direction. Fig. 3 illustrates the scenario where the TE_0 mode is input at Port1, and any of the TE_0 , TE_1 , and TE_2 modes can be observed at Port2.

For our device, the TO effect is observed by the introduction of thermo-optic coefficient of $-8 \times 10^{-5}/^\circ\text{C}$ of the polymer material [49]. For a phase change of π at any MZI branch of THMCs, a temperature change of $\sim 7^\circ\text{C}$ is needed and that for TWMC the temperature change is $\sim 8.25^\circ\text{C}$. The different mode conversion functionalities of the device are summarized in Table I.

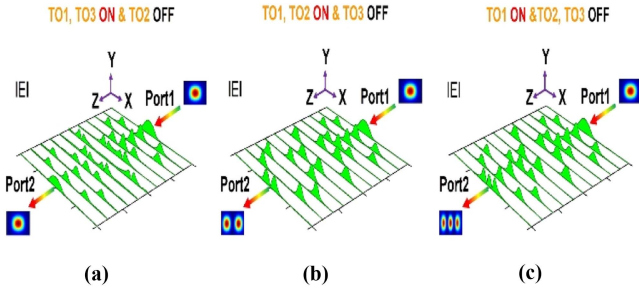














Fig. 3. Evolution of mode electric field ($|E|$) profile at the different positions of light propagation through the device when TE_0 is inputted. (a) TE_0 to TE_0 , (b) TE_0 to TE_1 and (c) TE_0 to TE_2 .

TABLE I
VARIOUS (TE) MODE CONVERSION FUNCTIONALITIES OF THE TO BASED MZI DEVICE

Input (Port1)	Heater Electrodes			Output (Port2)
	TO1	TO2	TO3	
TE_0 	ON	OFF	ON	TE_0 
	ON	ON	OFF	TE_1 
	ON	OFF	OFF	TE_2 
TE_1 	OFF	ON	ON	TE_0 
	OFF	OFF	OFF	TE_1 
	OFF	ON	OFF	TE_2 
TE_2 	OFF	OFF	ON	TE_0 
	OFF	ON	OFF	TE_1 
	OFF	OFF	OFF	TE_2 

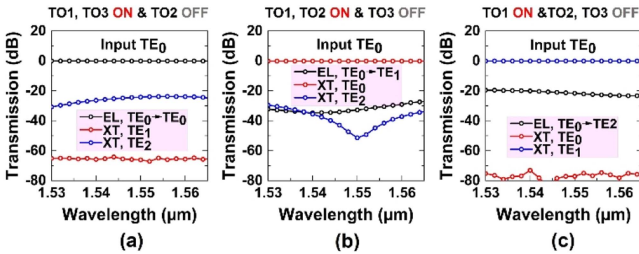


Fig. 4. Mode conversion simulated results for TE_0 input. (a) TE_0 to TE_0 , (b) TE_0 to TE_1 and (c) TE_0 to TE_2 .

We investigate the simulation results for the evaluation of the device performance. In simulation results, the material loss is not included. Fig. 4 shows the transmission characteristics (normalized) when TE_0 mode is input at Port1 and any of TE_0 , TE_1 and TE_2 modes is output from Port2. In this case, the excess loss (EL) is between 0.06 dB and 0.13 dB over the whole C band with MCE of 97.07% to 99.01% (by deduction of EL). The EL is high for conversion of TE_0 mode to TE_2 mode and this is reasonable because higher-order modes are prone to bends and radiation loss. The XTs, at the wavelength of $1.55 \mu\text{m}$, are between -21.68 dB and -77.10 dB and between -19.52 dB and -83.91 dB over the entire C band for all conversions of TE_0 mode.

Figs. 5 and 6 depicts the simulation results for conversion of TE_1 and TE_2 modes to TE_0 , TE_1 and TE_2 , respectively. From

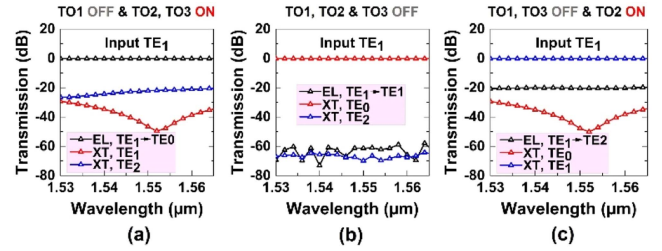


Fig. 5. Mode conversion simulated results for TE_1 input. (a) TE_1 to TE_0 , (b) TE_1 to TE_1 and (c) TE_1 to TE_2 .

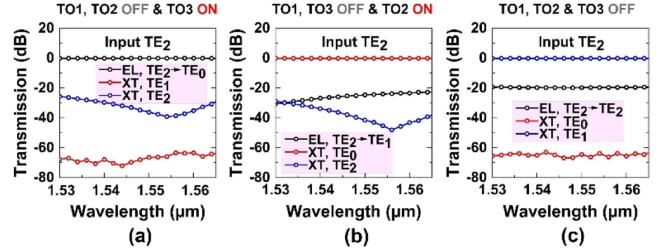


Fig. 6. Mode conversion simulated results for TE_2 input. (a) TE_2 to TE_0 , (b) TE_2 to TE_1 and (c) TE_2 to TE_2 .

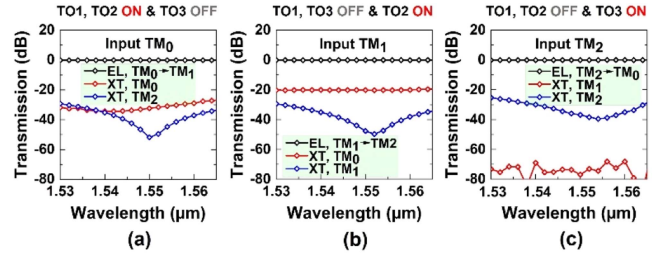


Fig. 7. Mode conversion simulated results for (a) TM_0 to TM_1 , (b) TM_1 to TM_2 and (c) TM_2 to TM_0 .

Fig. 5, the TE_1 mode conversion possesses the highest EL of 0.15 dB with MCE of 96.59%. The XTs are below -19.76 dB for the whole C band. For the conversion of TE_2 mode (Fig. 6), the EL is lower than 0.19 dB with MCE $>95.82\%$. The XTs are below -19.23 dB in the entire C band. The full-vector simulation, for three TM modes, namely fundamental mode (TM_0), first-order mode (TM_1) and second-order mode (TM_2), exhibits almost the same performance as that of TE modes which confirms the negligible polarization dependency of the device. The simulation results for TM_0 to TM_1 , TM_1 to TM_2 and TM_2 to TM_0 are presented in Fig. 7. For all three TM mode conversions, the ELs are between 0.10 dB and 0.15 dB and XTs stay in the range of -19.43 dB to -87.56 dB with MCE above 96.51% in the entire C band.

V. FABRICATION AND CHARACTERIZATION

We experimentally demonstrated our device in polymer materials to take advantage of their ease of processing and reproduction, outstanding thermo-optic property, index compatibility with traditional fiber, and simple coupling [64], [65]. Commercially available polymer materials EpoCore and EpoClad

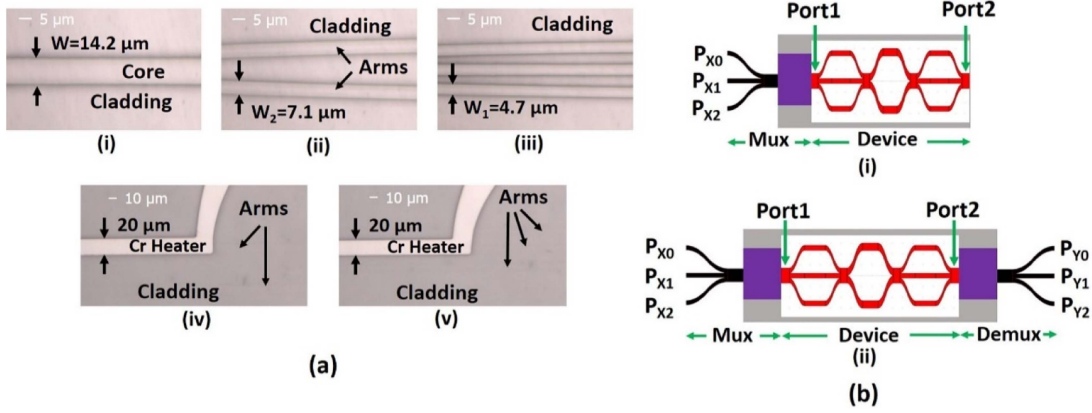


Fig. 8. (a) Microscopic images of our demonstrated device (i) three-mode section, (ii) Y-junction for TWMC, (iii) Y-junction for THMC, (iv) Cr electrode on TWMC, (v) Cr electrode on THMC and (b) schematic diagram for (i) observation of mode field patterns and (ii) transmission characteristics.

(Micro Resist Technology GmbH) was used as the core and cladding materials, respectively, to fabricate the device. The measured refractive indices of EpoCore and EpoClad with a prism coupler for TE polarization at $1.536 \mu\text{m}$ were 1.569 and 1.559, respectively. The device was fabricated in the cleanroom facilities using conventional microfabrication technology. A thin layer ($\sim 100 \text{ nm}$) of Chromium (Cr) was introduced as the metal electrode on top of the device. For THMCs, the length of the electrode was $2000 \mu\text{m}$ and that for TWMC was $1500 \mu\text{m}$ and the same width of $20 \mu\text{m}$ was used for both type of converters. Fig. 8(a) shows the microscopic images of different portions of the device.

For observing mode field patterns, light of the desired wavelength from a tunable laser source (81940A, Keysight Technology) was launched into the single-mode waveguide of the Mux [12] (P_{X0} , P_{X1} , and P_{X2}), Fig. 8(b)(i), using a single-mode fiber connected to the source. The Mux and the device propagated the coupled light through it and the output light was focused to the camera by an objective lens. Four heater probes with micro-positioners were used to provide the electric power to the Cr electrodes for activation of the TO effects. The polarization (TE or TM) was controlled through the adjustment of a polarization controller and a polarizer at the input and output terminals, respectively. For capturing the observed mode field patterns on the computer screen, a CCD camera (C10633, Hamamatsu Photonics) was used. The different TE mode field patterns observed from our fabricated device at different TO conditions are shown in Table II. The required electric power to turn on TO1, TO2 and TO3 electrodes are 6.7 mW, 8.4 mW and 6.6 mW, respectively. The response time of our device is less than 1.62 ms. All observed TE mode patterns adequately follow the simulation performance listed in Table I.

For further characterization, we evaluated the C-band wavelength dependency of the device. In that case, the light was launched into the Mux [12] inputs (P_{X0} , P_{X1} , and P_{X2}) and the output power was measured from the Demux [12] outputs (P_{Y0} , P_{Y1} , and P_{Y2}), Fig. 8(b)(ii), by a power meter (Newport 2832-C). The measured transmission characteristics (normalized to input) are shown in Figs. 9, 10, and 11 for the launched TE₀, TE₁ and

TABLE II
OBSERVED (TE) MODE FIELD PATTERNS (AT PORT2) OF THE PROPOSED DEVICE

Input Ports	Heater Electrodes			Output (Port2)		
	TO1	TO2	TO3	1.53 μm	1.55 μm	1.565 μm
P_{X0} (TE ₀)	ON	OFF	ON			
	ON	ON	OFF			
	ON	OFF	OFF			
P_{X1} (TE ₁)	OFF	ON	ON			
	OFF	OFF	OFF			
	OFF	ON	OFF			
P_{X2} (TE ₂)	OFF	OFF	ON			
	OFF	ON	OFF			
	OFF	OFF	OFF			

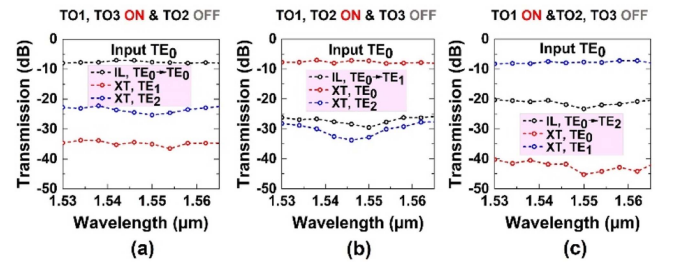


Fig. 9. Measured transmission results for TE₀ input. (a) TE₀ to TE₀, (b) TE₀ to TE₁ and (c) TE₀ to TE₂.

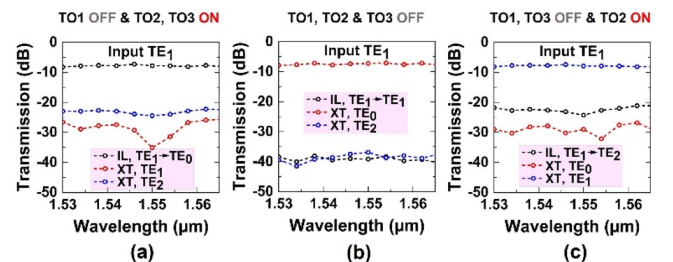


Fig. 10. Measured transmission results for TE₁ input. (a) TE₁ to TE₀, (b) TE₁ to TE₁ and (c) TE₁ to TE₂.

TABLE III
MODE FIELD PATTERNS (TE) OBSERVED AT DEMUX END OF THE DEVICE

Input Ports	Heater Electrodes			Output Ports								
	TO1	TO2	TO3	1.530 μm			1.550 μm			1.565 μm		
				P _{Y0} (TE ₀)	P _{Y1} (TE ₁)	P _{Y2} (TE ₂)	P _{Y01} (TE ₀)	P _{Y1} (TE ₁)	P _{Y2} (TE ₂)	P _{Y0} (TE ₀)	P _{Y1} (TE ₁)	P _{Y2} (TE ₂)
P _{X0} (TE ₀)	ON	OFF	ON									
	ON	ON	OFF									
	ON	OFF	OFF									
P _{X1} (TE ₁)	OFF	ON	ON									
	OFF	OFF	OFF									
	OFF	ON	OFF									
P _{X2} (TE ₂)	OFF	OFF	ON									
	OFF	ON	OFF									
	OFF	OFF	OFF									

TABLE IV
COMPARISON OF OUR DEVICE WITH RECENTLY PUBLISHED WORKS

Ref.	Dynamic Operation	Polarization Insensitivity	Mode Conversion	Max. Power	Max. XT and/or Min. MCE (C band)	Material Platform and Fabrication Cost
[35]	No	Weakly sensitive	LP ₀₁ to LP _{11a} or LP ₀₁ to LP _{11b}	-	90%	Polymer/ Low (UVL)
[39]	No	No	TE ₀ to TE ₁ or TE ₀ to TE ₂	-	-6.3 dB	SOI/High (EBL)
[40]	No	No	TE ₀₀ or TE ₁₀	-	82.6% (-0.830 dB)	SOI/ High (EBL)
[43]	No	No	E ₀₀ to E ₂₀	-	67% (-1.741 dB)	Theoretical study
[44]	No	No	LP ₀₁ to LP _{11a} or LP ₀₁ to LP _{11b}	-	89.2%	CWG*/Medium (FsLDW**)
[49]	Yes	Yes	Between TE ₀ (TM ₀) to TE ₂ (TM ₂)	7.66 mW	-	Polymer/Low (UVL)
[50]	Yes	No	Between TE ₀ and TE ₁	-	-	Theoretical study
[51]	Yes	No	Among TE ₀ , TE ₁ and TE ₂	106.69 mW	-14.3 dB	SOI/High (EBL)
[52]	Yes	No	Among first four TE modes	75 mW	-16.6 dB	SOI/High (EBL)
[53]	Yes	No	Among first three TE modes	16.6 mW	-13.0 dB	SOI/High (EBL)
[54]	Yes	Yes	Among four LP modes (TE/TM)	10.5 mW	96.5% (1.55 μm)	Polymer/Low or Medium (multi-step UVL or FsLDW)
Our work	Yes	Yes	Among first three modes (TE/TM)	8.4 mW	-18.9 dB/92.5%	Polymer/Low (UVL)

*Composite waveguide (CWG), **Femtosecond laser direct writing (FsLDW)

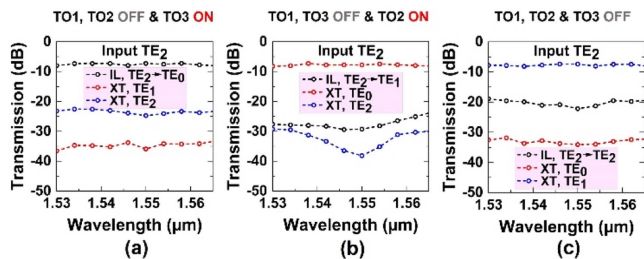


Fig. 11. Measured transmission results for TE₂ input. (a) TE₂ to TE₀, (b) TE₂ to TE₁ and (c) TE₂ to TE₂.

TE₂ modes, respectively. All power is calculated only for our device by deducting the losses of the Mux and Demux [12].

From Fig. 9(a), for TE₀ to TE₀ transmission, the IL is between 7.1 dB and 8.0 dB over the whole C band. The XTs are between -33.8 dB and -36.5 dB and between -22.3 dB and -25.3 dB for TE₁ and TE₂ modes, respectively, with MCE higher than 96.2%. At 1.55 μm , the XTs are below -25.3 dB and MCE is

upper than 98.1%. The IL is in the range of 7.0 dB to 8.2 dB for TE₀ to TE₁ mode conversion in the entire C band (Fig. 9(b)). The XTs lies below -25.7 dB and MCE is >97.2% for C band while XTs are less than -29.1 dB with MCE 99.1% at 1.55 μm . From Fig. 9(c), TE₀ to TE₂ mode conversion, the IL is between 7.2 dB and 8.3 dB in the entire C band. The XTs are lower than -20.3 dB and -40.2 dB for TE₀ and TE₁ mode, respectively, with MCE above 94.1%. For 1.55 μm , the XTs are <-23.3 dB and MCE is >97.3%.

For TE₁ to TE₀ mode conversion (Fig. 10(a)), the IL is below 8.2 dB in the entire C band. The XTs remain below -25.6 dB and -22.3 dB for TE₁ mode and TE₂ mode, respectively, with MCE > 94.8%. XTs are less than -24.5 dB and MCE is >97.7% at 1.55 μm . For other two conversions (TE₁ to TE₁ and TE₁ to TE₂), the IL is lower than 8.1 dB and the XTs are below -21.1 dB with MCE above 94.0% over the C band. For 1.55 μm , the XTs are below -24.3 dB and the MCE is >97.0%. From, Fig. 11, the IL is lower than 8.2 dB, and the XTs are below -18.9 dB and the MCE is above 92.5% for the whole C band. At 1.55 μm , the XTs

are less than -22.2 dB and the MCE is $>96.6\%$. Table III shows all of the mode field patterns (TE) observed at the Demux end.

For our fabricated device, the measured IL is lower than 8.3 dB for TE polarization. The IL includes the material loss (2.5 dB/cm), the fiber-to-device coupling loss at the input port (2.4 dB), and excess loss (1.6 dB). By utilizing low loss material and improving the fabrication process, the IL can be greatly reduced [66], [64]. The simulated and experimental results of the device verify the mode conversion functionalities of our proposed device. A comparison of our device with recently published ones are show in Table IV.

From the Table, it is obvious that although two designs, [52] and [54], support more (four) modes, our three-mode converter consume relatively less power except [49] which can convert only between TE_0 (TM_0) and TE_2 (TM_2) modes and unable to deal with TE_1 (TM_1) mode. Our device is also almost polarization-independent which eliminate the need of polarization splitter/combiner and can be applied in PDM system [57], [58]. Furthermore, the device possess simple structure and hence conventional low cost UVL is enough to fabricate it [58], [59].

VI. CONCLUSION

We presented a reconfigurable three-mode converter for the MDM optical networks that can convert among any of TE_0 , TE_1 , and TE_2 modes by the activation or deactivation of TO effects. The device operation is validated numerically and the experimental results fairly follows the simulation performance of the device. For all mode conversions, our fabricated device exhibits maximum IL of 7.9 dB and XTs of lower than -22.2 dB and MCE above 96.6% at $1.55 \mu\text{m}$. The device consumes relatively low power and is polarization-insensitive. Our suggested mode converter can be a good fit for improving the flexibility of MDM optical networks.

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